2.5V Drive Pch+SBD MOSFET

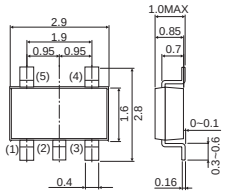
QS5U26

●**Structure**
Silicon P-channel MOSFET
Schottky Barrier DIODE

●**Features**
1) The QS5U26 combines Pch MOSFET with a Schottky barrier diode in a TSMT5 package.
2) Low on-state resistance with fast switching.
3) Low voltage drive (2.5V).
4) Built-in schottky barrier diode has low forward voltage.

●**Dimensions** (Unit : mm)

TSMT5



Each lead has same dimensions

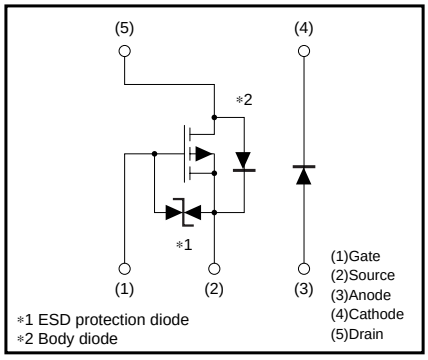
Abbreviated symbol : U26

●**Applications**
Switching

●**Packaging specifications**

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
QS5U26		○

●**Equivalent circuit**



∗1 ESD protection diode
∗2 Body diode

●Absolute maximum ratings (Ta=25°C)

<MOSFET>

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	–20	V
Gate-source voltage		V_{GSS}	±12	V
Drain current	Continuous	I_D	±1.5	A
	Pulsed	I_{DP} *1	±6.0	A
Source current (Body diode)	Continuous	I_S	–0.75	A
	Pulsed	I_{SP} *1	–3.0	A
Channel temperature		Tch	150	°C
Power Dissipation		P_D *3	0.9	W / ELEMENT

<Di>

Parameter	Symbol	Limits	Unit
Repetitive peak reverse voltage	V_{RM}	30	V
Reverse voltage	V_R	20	V
Forward current	I_F	0.5	A
Forward current surge peak	I_{FSM} *2	2.0	A
Junction temperature	Tj	150	°C
Power Dissipation	P_D *3	0.7	W / ELEMENT

<MOSFET AND Di>

Parameter	Symbol	Limits	Unit
Total power dissipatino	P_D *3	1.25	W / TOTAL
Range of strage temperature	Tstg	–55 to 150	°C

*1 Pw≤10µs, Duty cycle≤1% *2 60Hz・1cyc. *3 Mounted on a ceramic board.

●Electrical characteristics (Ta=25°C)

<MOSFET>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±10	µA	V_{GS}=±12V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	–20	–	–	V	I_D=–1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	–1	µA	V_{DS}=–20V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	–0.7	–	–2.0	V	V_{DS}=–10V, I_D=–1mA
Static drain-source on-starte resistance	$R_{DS\ (on)}$ *	–	160	200	mΩ	I_D=–1.5A, V_{GS}=–4.5V
		–	180	240	mΩ	I_D=–1.5A, V_{GS}=–4V
		–	260	340	mΩ	I_D=–0.75A, V_{GS}=–2.5V
Forward transfer admittance	$\|Y_{fs}\|$ *	1.0	–	–	S	V_{DS}=–10V, I_D=–0.75A
Input capacitance	C_{iss}	–	325	–	pF	V_{DS}=–10V
Output capacitance	C_{oss}	–	60	–	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	–	40	–	pF	f=1MHz
Turn-on delay time	$t_{d\ (on)}$ *	–	10	–	ns	I_D=–0.75A
Rise time	t_r *	–	10	–	ns	V_{DD}≒–15V
Turn-off delay time	$t_{d\ (off)}$ *	–	35	–	ns	V_{GS}=–4.5V
Fall time	t_f *	–	10	–	ns	R_L=20Ω
						R_G=10Ω
Total gate charge	Q_g	–	4.2	–	nC	V_{DD}≒–15V
Gate-source charge	Q_{gs}	–	1.0	–	nC	V_{GS}=–4.5V
Gate-drain charge	Q_{gd}	–	1.1	–	nC	I_D=–1.5A

* Pulsed

<Body diode (source–drain)>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}	–	–	–1.2	V	I_S=–0.75A, V_{GS}=0V

<Di>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	–	0.36	V	I_F=0.1A
		–	–	0.47	V	I_F=0.5A
Reverse current	I_R	–	–	100	µA	V_R=20V

●**Electrical characteristic curves**

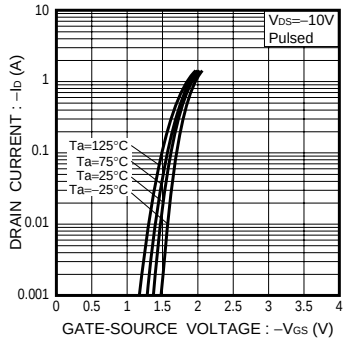


Fig.1 Typical Transfer Characteristics

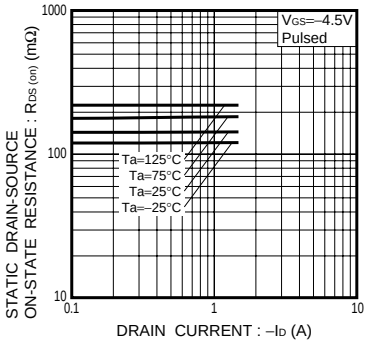


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (I)

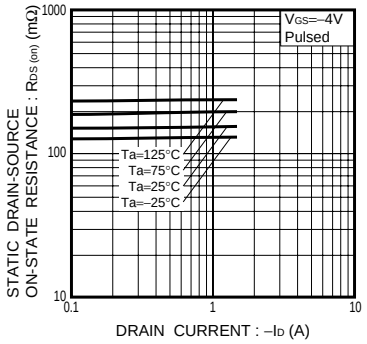


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (II)

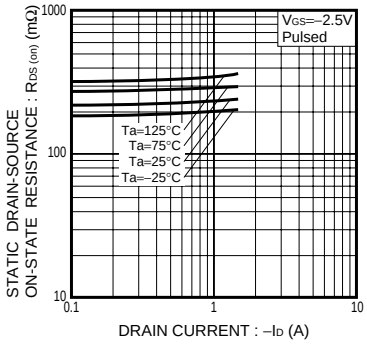


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (III)

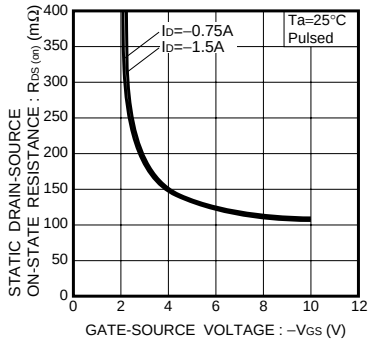


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

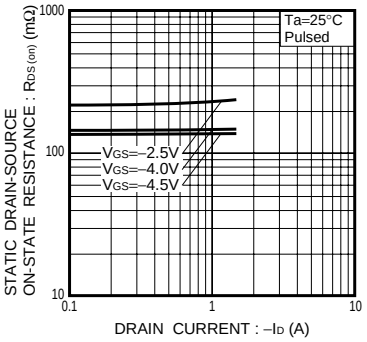


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current (Ⅳ)

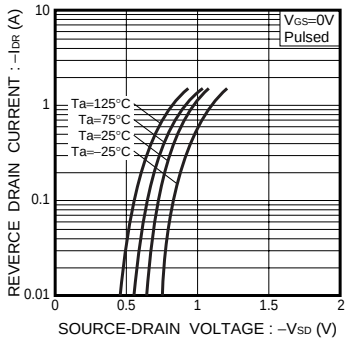


Fig.7 Reverse Drain Current vs. Source-Drain Current

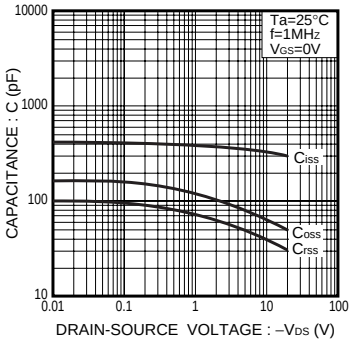


Fig.8 Typical Capacitance vs. Drain-Source Voltage

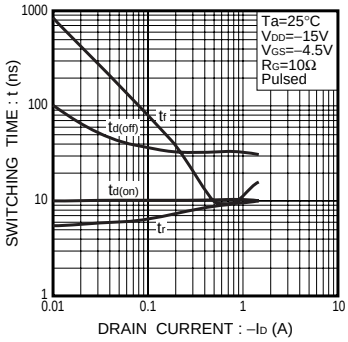


Fig.9 Switching Characteristics

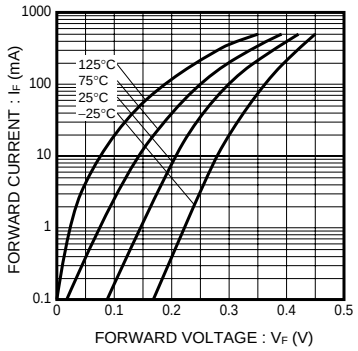


Fig.10 Forward Current vs. Forward Voltage

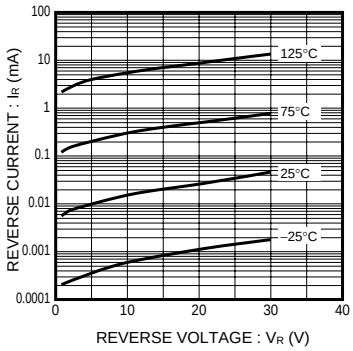


Fig.11 Reverse Current vs. Reverse Voltage

●Notice

SBD has a large reverse leak current compared to other type of diode. Therefore; it would raise a junction temperature, and increase a reverse power loss. Further rise of inside temperature would cause a thermal runaway.

This built-in SBD has low V_F characteristics and therefore, higher leak current. Please consider enough the surrounding temperature, generating heat of MOSFET and the reverse current.

Notes

No copying or reproduction of this document, in part or in whole, is permitted without the consent of ROHM CO.,LTD.

The content specified herein is subject to change for improvement without notice.

The content specified herein is for the purpose of introducing ROHM's products (hereinafter "Products"). If you wish to use any such Product, please be sure to refer to the specifications, which can be obtained from ROHM upon request.
Examples of application circuits, circuit constants and any other information contained herein illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.

Great care was taken in ensuring the accuracy of the information specified in this document. However, should you incur any damage arising from any inaccuracy or misprint of such information, ROHM shall bear no responsibility for such damage.

The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM and other parties. ROHM shall bear no responsibility whatsoever for any dispute arising from the use of such technical information.

The Products specified in this document are intended to be used with general-use electronic equipment or devices (such as audio visual equipment, office-automation equipment, communication devices, electronic appliances and amusement devices).

The Products are not designed to be radiation tolerant.

While ROHM always makes efforts to enhance the quality and reliability of its Products, a Product may fail or malfunction for a variety of reasons.

Please be sure to implement in your equipment using the Products safety measures to guard against the possibility of physical injury, fire or any other damage caused in the event of the failure of any Product, such as derating, redundancy, fire control and fail-safe designs. ROHM shall bear no responsibility whatsoever for your use of any Product outside of the prescribed scope or not in accordance with the instruction manual.

The Products are not designed or manufactured to be used with any equipment, device or system which requires an extremely high level of reliability the failure or malfunction of which may result in a direct threat to human life or create a risk of human injury (such as a medical instrument, transportation equipment, aerospace machinery, nuclear-reactor controller, fuel-controller or other safety device). ROHM shall bear no responsibility in any way for use of any of the Products for the above special purposes. If a Product is intended to be used for any such special purpose, please contact a ROHM sales representative before purchasing.

If you intend to export or ship overseas any Product or technology specified herein that may be controlled under the Foreign Exchange and the Foreign Trade Law, you will be required to obtain a license or permit under the Law.

Thank you for your accessing to ROHM product informations.
More detail product informations and catalogs are available, please contact your nearest sales office.

ROHM Customer Support System

THE AMERICAS / EUROPE / ASIA / JAPAN

www.rohm.com

Contact us : webmaster@ rohm.co.jp

ROHM CO., LTD. 21 Saiin Mizosaki-cho, Ukyo-ku, Kyoto 615-8585, Japan
TEL : +81-75-311-2121
FAX : +81-75-315-0172

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ROHM Semiconductor:

QS5U26TR